Yimao Cai

List of Publications by Year in descending order

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24	1,327	567281 15	794594 19
papers	citations	h-index	g-index

24	24	24	1865
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Non-Linear Resistive Switching Characteristics in HFO2-Based RRAM with Low-Dimensional Material Engineered Interface. , 2021, , .		1
2	Investigation of Non-Linear Selection Effect on RRAM based Neuromorphic Computing Array with Passive Selective Element. , 2021, , .		0
3	A TaOx-Based RRAM with Improved Uniformity and Excellent Analog Characteristics by Local Dopant Engineering. Electronics (Switzerland), 2021, 10, 2451.	3.1	9
4	In-memory computing with emerging nonvolatile memory devices. Science China Information Sciences, 2021, 64, 1.	4.3	31
5	Adaptive Random Number Generator Based on RRAM Intrinsic Fluctuation for Reinforcement Learning. , 2020, , .		2
6	Self-Activation Neural Network Based on Self-Selective Memory Device With Rectified Multilevel States. IEEE Transactions on Electron Devices, 2020, 67, 4166-4171.	3.0	23
7	Memory materials and devices: From concept to application. InformaÄnÃ-MateriÃ¡ly, 2020, 2, 261-290.	17.3	181
8	A Memristor-Based In-Memory Computing Network for Hamming Code Error Correction. IEEE Electron Device Letters, 2019, 40, 1080-1083.	3.9	17
9	Thermal effect in ultra-high density 3D vertical and horizontal RRAM array. Physica Scripta, 2019, 94, 045001.	2.5	8
10	Ion Gated Synaptic Transistors Based on 2D van der Waals Crystals with Tunable Diffusive Dynamics. Advanced Materials, 2018, 30, e1800195.	21.0	368
11	Improvement of HfO_x-Based RRAM Device Variation by Inserting ALD TiN Buffer Layer. IEEE Electron Device Letters, 2018, 39, 819-822.	3.9	57
12	Enhancement of HfO2 Based RRAM Performance Through Hexagonal Boron Nitride Interface Layer. , 2018, , .		1
13	Study on High-Resistance State Instability of TaOx-Based RRAM. , 2018, , .		0
14	Bipolar to unipolar mode transition and imitation of metaplasticity in oxide based memristors with enhanced ionic conductivity. Journal of Applied Physics, 2018, 124, .	2.5	19
15	Tolerance of intrinsic device variation in fuzzy restricted Boltzmann machine network based on memristive nano-synapses. Nano Futures, 2017, 1, 015003.	2.2	11
16	Multifunctional Nanoionic Devices Enabling Simultaneous Heterosynaptic Plasticity and Efficient Inâ€Memory Boolean Logic. Advanced Electronic Materials, 2017, 3, 1700032.	5.1	56
17	Modulation of nonlinear resistive switching behavior of a TaO_x-based resistive device through interface engineering. Nanotechnology, 2017, 28, 055204.	2.6	35
18	Self-selection effects and modulation of TaOx resistive switching random access memory with bottom electrode of highly doped Si. Journal of Applied Physics, 2016, 119, 195302.	2.5	17

#	ARTICLE	IF	CITATIONS
19	Microscopic origin of read current noise in TaOx-based resistive switching memory by ultra-low temperature measurement. Applied Physics Letters, 2016, 108, .	3.3	8
20	Engineering incremental resistive switching in TaO<sub>x</sub based memristors for brain-inspired computing. Nanoscale, 2016, 8, 14015-14022.	5.6	271
21	Novel Vertical 3D Structure of TaOx-based RRAM with Self-localized Switching Region by Sidewall Electrode Oxidation. Scientific Reports, 2016, 6, 21020.	3.3	72
22	A flexible organic resistance memory device for wearable biomedical applications. Nanotechnology, 2016, 27, 275206.	2.6	67
23	Record Low-Power Organic RRAM With Sub-20-nA Reset Current. IEEE Electron Device Letters, 2013, 34, 223-225.	3.9	34
24	A New Dynamic Selector Based on the Bipolar RRAM for the Crossbar Array Application. IEEE Transactions on Electron Devices, 2012, 59, 2277-2280.	3.0	39